

**DRAFT - FOR EXAMINER REVIEW ONLY  
NOT FOR FILING**

Attorney Docket No. YAO-3950US2  
PATENT

In re Application of  
Yoshihisa Nagano et al.

: Group Art Unit: 2815  
: Examiner: Jose R. Diaz

Serial No.: 10/170,168

Filed: June 12, 2002

For: SEMICONDUCTOR DEVICE AND METHOD FOR FABRICATING THE SAME

**AMENDMENT UNDER 37 C.F.R. § 1.111**

**IN THE CLAIMS:**

Please amend claims 28 and add new claim 47 as follows.

1. (Currently amended) A method for fabricating a semiconductor device,  
comprising the step of:

sequentially forming a lower electrode, a dielectric film comprising ~~either~~  
~~dielectric material having a high dielectric constant or~~ a ferroelectric ~~[material]~~ film, and  
an upper electrode on a supporting substrate ~~(having an integrated)~~, thereby forming a  
capacitor;

forming a first interlayer insulating film provided so as to cover the capacitor;

forming a first contact hole in the first interlayer insulating film;